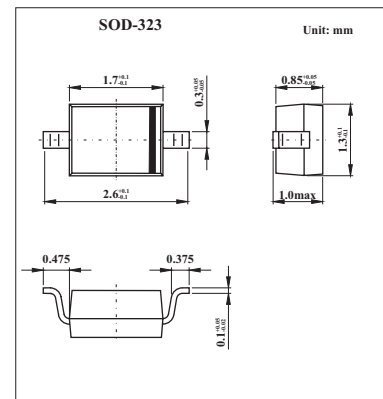


SCHOTTKY DIODE

SD107WS



■ Features

- Low turn-on voltage
- Fast switching
- Microminiature plastic package
- These devices are protected by a PN junction guard ring against excessive voltage, such as electrostatic discharge.
- Ideal for protection of MOS devices, steering, blasing, and coupling diodes for fast switching and low logic level applications.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Value	Unit
Continuous Reverse Voltage	V_R	30	Volts
Forward Current	I_F	100	mA
Forward Surge Current, $t_p = 10$ ms	I_{FSM}	0.75	A
Power Dissipation $T_c = 25^\circ\text{C}$	P_{tot}	250(Notes 1)	mW
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	500	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_s	-65 to +150	$^\circ\text{C}$

Note:

1. Valid provided that electrodes are kept at ambient temperature

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Characteristic	Symbol	Min	Typ	Max	Unit
Reverse Breakdown Voltage at $I_R = 100 \mu\text{A}$	BV_R	30			Volts
Leakage Current at $V_R = 25\text{V}$	I_R			1000	μA
Forward Voltage	V_F	at $I_F = 2.1\text{mA}$	260		mV
		at $I_F = 15\text{mA}$	360		
		at $I_F = 100\text{mA}$	470	550	
		at $I_F = 200\text{mA}$	580	880	
Junction Capacitance at $V_R = 10\text{V}$, $f = 1.0\text{MHz}$	C_{tot}			7.0	pF

■ Marking

Marking	S1
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